2N3766, 2N3767



NPN Power Silicon Transistor

Rev. V4

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/518
- TO-66 Package
- Designed for High Speed Switching and High Voltage Amplifier Applications



Electrical Characteristics (25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.			
Off Characteristics								
Collector - Emitter Breakdown Voltage	I_C = 100 mA dc, 2N3766 I_C = 100 mA dc, 2N3767	V _{(BR)CEO}	V dc	60 80	_			
Collector - Base Cutoff Current	VCB = 80 Vdc 2N3766 VCB = 100 V dc 2N3767	I _{CBO}	μA dc	_	10 10			
Collector - Emitter Cutoff Current	V _{CE} = 60 V dc 2N3766 V _{CE} = 80 V dc 2N3767	I _{CEO}	μA dc	_	500			
Collector - Emitter Cutoff Current	V_{CE} = 80 V dc, V_{BE} = 1.5 Vdc, 2N3766 V_{CE} = 100 Vdc, V_{BE} = 1.5 Vdc, 2N3767	I _{CEX1}	μA dc	_	10 10			
Collector - Emitter Cutoff Current	$T_A = +150^{\circ}\text{C}$ $V_{BE} = 1.5 \text{ V dc}$ $V_{CE} = 50 \text{ V dc}, 2N3766$ $V_{CE} = 70 \text{ V dc}, 2N3767$	I _{CEX2}	mA dc	_	1.0 1.0			
Emitter - Base Cutoff Current	V _{EB} = 6 V dc	I _{EBO}	μA dc	_	500			
On Characteristics								
Forward Current Transfer Ratio	$V_{CE} = 5 \text{ V dc}, \ I_{C} = 50 \text{ mA dc}$ rrent Transfer Ratio $V_{CE} = 5 \text{ V dc}, \ I_{C} = 500 \text{ mA dc}$ $V_{CE} = 10 \text{ V dc}, \ I_{C} = 1 \text{ A dc}$		-	30 40 20	160			
Forward Current Transfer Ratio	Forward Current Transfer Ratio $T_A = -55^{\circ}C$ $V_{CE} = 5.0 \text{ V dc}, I_C = 0.5 \text{ A dc}$		-	13				
Base - Emitter Voltage (non-saturated)	V _{CE} = 10 V dc, I _C = 1.0 A dc	V_{BE}	V dc	_	1.5			
Collector - Emitter Voltage (saturated)	I _C = 1.0 A dc, I _B = 0.1 A dc	V _{CE(SAT)1}	V dc	_	2.5			
Collector - Emitter Voltage (saturated)	I _C = 0.5 A dc, I _B = 0.05 A dc	V _{CE(SAT)2}	V dc	_	1.0			
Base - Emitter Voltage (saturated)	$I_C = 1.0 \text{ A dc}, I_B = 0.1 \text{ A dc}$	V _{BE(SAT)1}	V dc	_	1.5			



NPN Power Silicon Transistor

Rev. V4

Dynamic Characteristics							
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio	V _{CE} = 10 V dc, I _C = 500 mA dc, f = 10 MHz	h _{FE}	-	1	8		
Open Capacitance (Open Circuit)	$V_{CB} = 10 \text{ V dc}, I_E = 0, 0.1 \text{ MHz} \le f \le 1 \text{ MHz}$	C_{obo}	pF	_	50		

Absolute Maximum Ratings (25°C unless otherwise specified)

Ratings	Symbol	Value
Collector - Emitter Voltage 2N3766 2N3767	V _{CEO}	60 V dc 80 V dc
Collector - Base Voltage 2N3766 2N3767	V _{CBO}	80 V dc 100 V dc
Emitter - Base Voltage	V _{EBO}	6.0 V dc
Base Current	l _Β	2.0 A dc
Collector Current	I _C	4.0 A dc
Total Power Dissipation @ T _C = +25°C ¹	P _T	25 W
Junction & Storage Temperature Range	T _J , T _{STG}	-65°C to +200°C

^{1.} Between T_C = +25°C and T_C = +200°C, linear derating factor (average) = 143m/W°C.

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{\theta JC}$	7.0°C/W

2N3766, 2N3767



NPN Power Silicon Transistor

Rev. V4

Electrical Characteristics (25°C unless otherwise specified)

ulse Response Test Conditions		Symbol	Units	Min.	Max.
Turn-On Time	V_{CC} = 30 V dc, I_{C} = 0.5 A dc, I_{B1} = 0.05 A dc	t _{on}	μs		0.25
Turn-Off Time	V_{CC} = 30 Vdc, I_{C} = 0.5 A dc, I_{B1} = I_{B2} = .05 A dc	t _{off}	μs	_	2.5

Safe Operating Area

DC Tests: $T_C = +25 \, ^{\circ}\text{C}$, I Cycle, $t = 1.0 \, \text{s}$

Test 1: $V_{CE} = 6.25 \text{ V dc}, I_{C} = 4 \text{ A dc}$

Test 2: $V_{CE} = 20 \text{ V dc}, I_{C} = 1.25 \text{ A dc}$

Test 3: $V_{CE} = 50 \text{ V dc}, I_{C} = 150 \text{ mA dc}, 2N3766$

 $V_{CE} = 65 \text{ V dc}, I_{C} = 150 \text{ mA dc}, 2N3767$

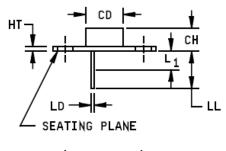


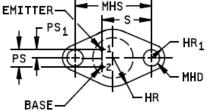
NPN Power Silicon Transistor

Rev. V4

Outline Drawing (TO-66)

Symbol	Inches		Millin	Notes	
	Min	Max	Min	Max	
CD		.620		15.76	
СН	.250	.340	6.35	8.64	
HR		.350		8.89	4
НТ	.050	.075	1.27	1.91	
HR ₁	.115	.145	2.92	3.68	4
LD	.028	.034	0.71	0.86	4, 6
LL	.360	.500	9.14	12.70	
L ₁		.050		1.27	6
MHD	.142	.152	3.61	3.86	4
MHS	.958	.962	24.33	24.43	
PS	.190	.210	4.83	5.33	3
PS ₁	.093	.107	2.36	2.72	3
s	.570	.590	14.48	14.99	





NOTES:

- Dimensions are in inches.
- 2. Millimeters are given for general information only.
- These dimensions should be measured at points .050 inch (1.27 mm) +.005 inch (0.13 mm) -.000 inch (0.00 mm) below seating plane. When gauge is not used, measurement will be made at the seating plane.
- Two places.
- The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
- Lead diameter shall not exceed twice LD within L₁.
- 7. Lead number 1 is the emitter, lead 2 is the base, case is the collector.
- In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.

FIGURE 1. Physical dimensions (similar to TO-66).



NPN Power Silicon Transistor

Rev. V4

Safe Operating Area

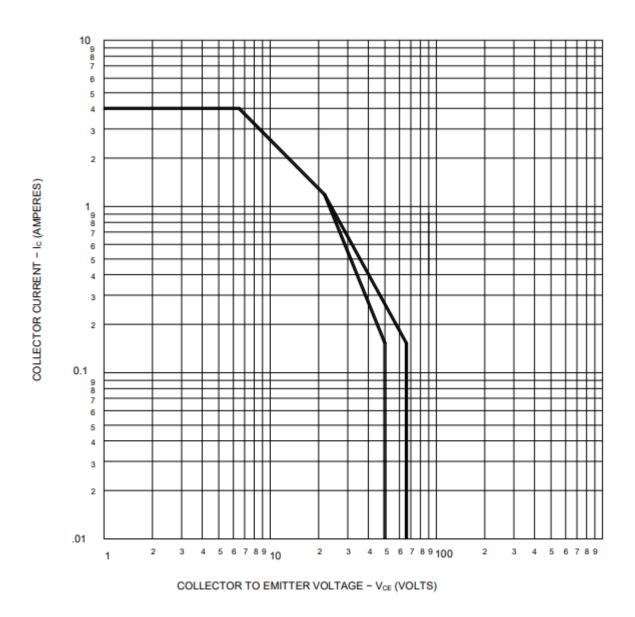


FIGURE 3. Maximum safe operating area graph (continuous dc) for types 2N3766 and 2N3767.

2N3766, 2N3767



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Rev. V4

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